

TOWARDS A MANAGEABLE THEORY FOR CROSS-GRATING HEED

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Under cross-grating conditions only a plane of reciprocal lattice points with vectors \underline{G} contributes significantly to the observed diffraction. Thus the electrons move in an effective two-dimensionally-varying 'projected' potential $U(\underline{R})$, with Fourier coefficients $U_{\underline{G}}$ (Berry 1971 - hereafter called I). The vector $\underline{R} (=R, \phi)$ lies in real space in the plane \underline{G} . Diffraction contrast arises from the beating of the different Bloch waves $b_j(\underline{r})$ as the specimen thickness z varies, the periodicities depending on the eigenvalues s_j , defined by

$$b_j(\underline{r}) = \tau_j(\underline{R}) \exp(-i s_j z / 2k) \quad (1)$$

(\underline{k} is the wave vector of the incident beam).

In conventional many-wave theory (Howie 1970), the condition for s_j arises from a Fourier analysis of $\tau_j(\underline{R})$, which leads to the following^j determinantal equation over the set of \underline{G} 's:

$$\det_{\underline{G}\underline{G}'} \left\| \left[s - (\underline{K}_0 + \underline{G})^2 \right] \delta_{\underline{G}\underline{G}'} - U_{\underline{G}-\underline{G}'} \right\| = 0 \quad (2)$$

(\underline{K}_0 is the component of \underline{k} in the plane \underline{G} , so that the angle of incidence θ is $|\underline{K}_0| / |\underline{k}|$). This procedure, which works well for the systematic case, runs into difficulties for cross-grating situations involving high energies and heavy atoms, because very large matrices arise.

We avoid this problem by using the KKR method of band-structure theory (Ziman 1971) in two dimensions, in which $\tau_j(\underline{R})$ is expanded within a single cell in angular momentum components $\tau_j^1(\underline{R}) \exp(i l \phi)$. Instead of (2), the condition for s_j is

$$\det_{\underline{l}\underline{l}'} \left\| (\cot \eta_{\underline{l}}(s) - i) \delta_{\underline{l}\underline{l}'} + B_{\underline{l}-\underline{l}'}(s, \underline{K}_0) \right\| = 0, \quad (3)$$

where $\eta_{\underline{l}}(s)$ is the l -wave phase shift for scattering from $U(\underline{R})$ (assumed to be a cylindrically symmetrical potential well within a single cell) at 'energy' s , while $B_{\underline{l}-\underline{l}'}$ is a 'structure constant', defined in terms of the lattice sites \underline{R}_j by

$$B_{\underline{m}}(s, \underline{K}_0) = \sum_{\underline{i} \neq \underline{o}} \exp(i \underline{K}_0 \cdot \underline{R}_i + i m \phi_{\underline{R}_i}) H_{\underline{m}}^{(1)}(\sqrt{s} R_i), \quad (4)$$

$H_{\underline{m}}^{(1)}$ being the Hankel function of the first kind.

This formalism brings out the separation between 'bound' ($s_j < 0$) and 'free' ($s_j > 0$) bands, which is known (I, p708) to simplify analysis of the systematic case. The bound bands, where $B_{\underline{m}}$ is very small, are centred

on the energy levels of $U(R)$, for which

$$\cot \eta_1(s) = i, \text{ i.e. } \eta_1(s) \longrightarrow -i\infty ; \quad (5)$$

these bands correspond to almost flat branches of the dispersion surface. The nearly-free bands associated with each \underline{G} - value satisfy

$$s = (\underline{G} + \underline{K}_0)^2 - \frac{4}{a^2} \sum_1 \tan \eta_1(|\underline{G} + \underline{K}_0|^2), \quad (6)$$

where a is the lattice spacing.

As in the systematic case, we expect the bound bands to dominate the observed diffraction (I, fig. 10ff). The total number of these is n , roughly given by

$$n = \int_0^\infty R |U(R)| dR/4, \quad (7)$$

which are distributed over the angular momenta 0 to l_{\max} , say. For $l > l_{\max}$ there are no bound states and the η_1 are negligible, even for $s > 0$. Thus the matrix in our eq. (3) has about l_{\max}^2 important elements, while the usual eq. (2) has at least n^2 important elements (many more are often required to ensure convergence). Now, n greatly exceeds l_{\max} , so that (3) is likely to be more useful in practice. As a numerical example, for Tungsten at 750kV, n is 18 while l_{\max} is only 5.

References

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